TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# 2SK2013

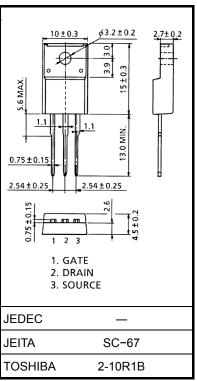
#### Audio Frequency Power Amplifier Application

- High breakdown voltage : V<sub>DSS</sub> = 180V
- High forward transfer admittance  $\therefore$  |Y<sub>fs</sub>| = 0.7 S (typ.)
- Complementary to 2SJ313

#### Absolute Maximum Ratings (Ta = 25°C)

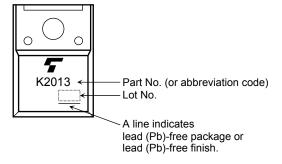
Characteristics	Symbol	Rating	Unit	
Drain-source voltage	V <sub>DSS</sub>	180	V	
Gate-source voltage	V <sub>GSS</sub>	±20	V	
Drain current (Note 1)	۱ <sub>D</sub>	1	А	
Drain power dissipation (Tc = 25°C)	PD	25	W	
Channel temperature	T <sub>ch</sub>	150	°C	
Storage temperature range	T <sub>stg</sub>	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 1.9 g (typ.)

#### Marking



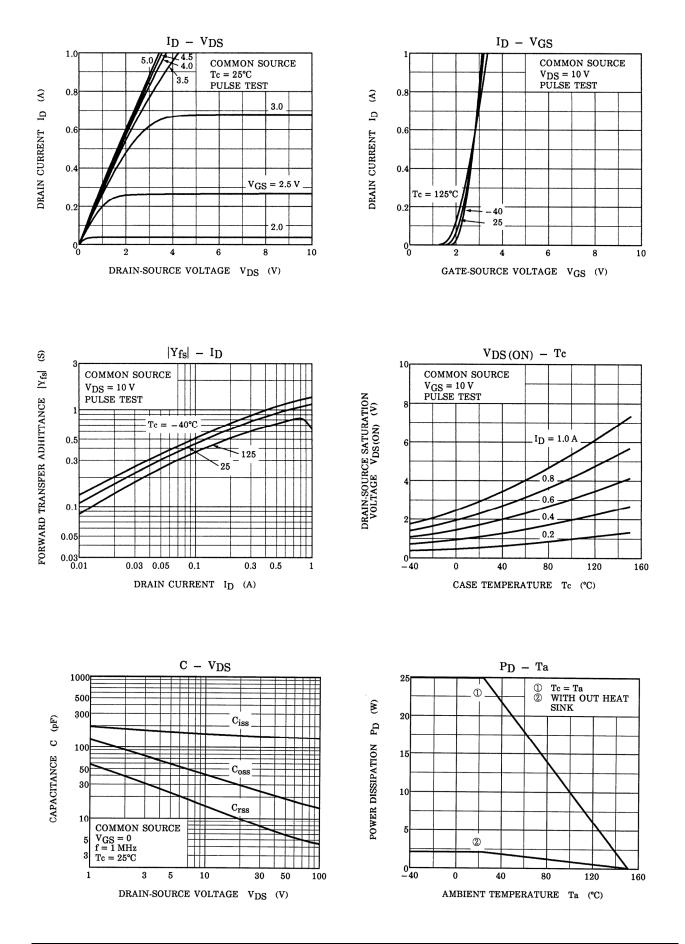
## **Electrical Characteristics (Ta = 25°C)**

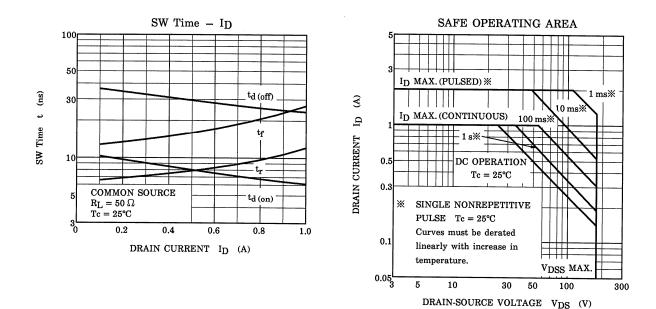
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{DS}$ = 0, $V_{GS}$ = ±20 V	—	_	±100	nA
Drain-source breakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0	180	_	—	V
Gate-source cut-off voltage (Note 2)	V <sub>GS (OFF)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 mA	1.8	_	2.8	V
Drain-source saturation voltage	V <sub>DS (ON)</sub>	I <sub>D</sub> = 0.6 A, V <sub>GS</sub> = 10 V	_	1.7	3.0	V
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.3 A	—	0.7	—	S
Input capacitance	C <sub>iss</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 0, f = 1 MHz	_	170	—	
Output capacitance	C <sub>oss</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 0, f = 1 MHz	_	45	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	V <sub>DD</sub> ≈ 10 V, V <sub>GS</sub> = 0, f = 1 MHz	_	17	_	

Note 1: Ensure that the channel temperature does not exceed 150  $^\circ\text{C}.$ 

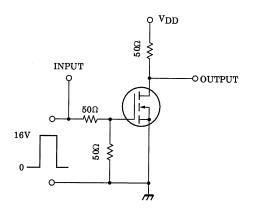
Note 2: V<sub>GS (OFF)</sub> Classification O: 0.8~1.6, This transistor is an electrostatic-sensitive device.

Please handle with caution.

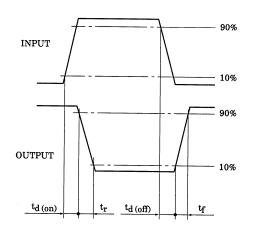




## **Switching Time Test Circuit**



## Waveforms



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20070701-EN

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